

Abstract**Silicon wafer for semiconductor and manufacturing method thereof**

5 A silicon wafer with high quality where both slip dislocation and warpage are suppressed to be considerably small, which is suitable for diameter enlargement, and a manufacturing method thereof are provided.

10 A silicon wafer where a density of BMDs with sizes of 20nm to 40nm of BMDs present at a deep position which is spaced from a surface of a silicon wafer by a distance equal to or more than 20 μ m is in a range of $5 \times 10^{11}/\text{cm}^3$ to $5 \times 10^{13}/\text{cm}^3$, and a density of BMDs with sizes of 300nm or more is equal to or less than $1 \times 10^7/\text{cm}^3$ is obtained.

15 Fig. 1